

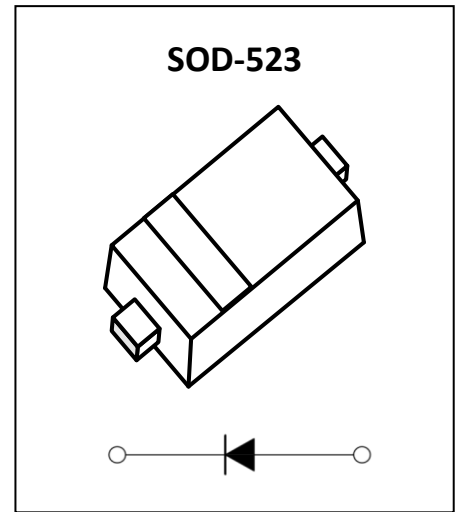


RB751S-40 Schottky Barrier Diode

Feature

- Small surface mounting type
- Low IR
- High Reliability

MARKING:



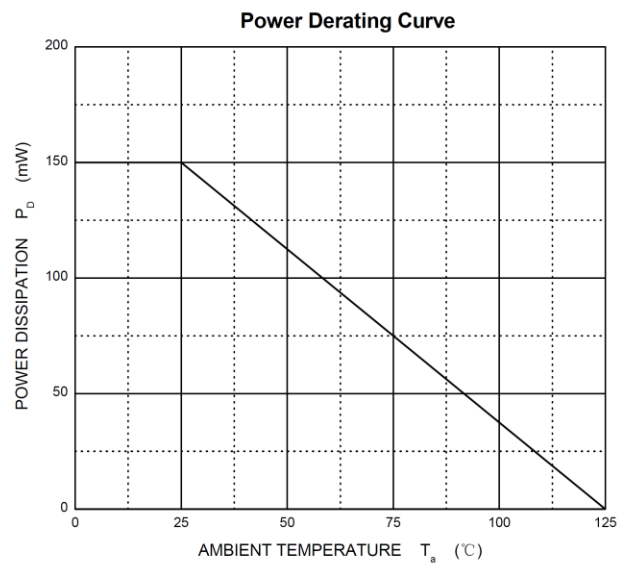
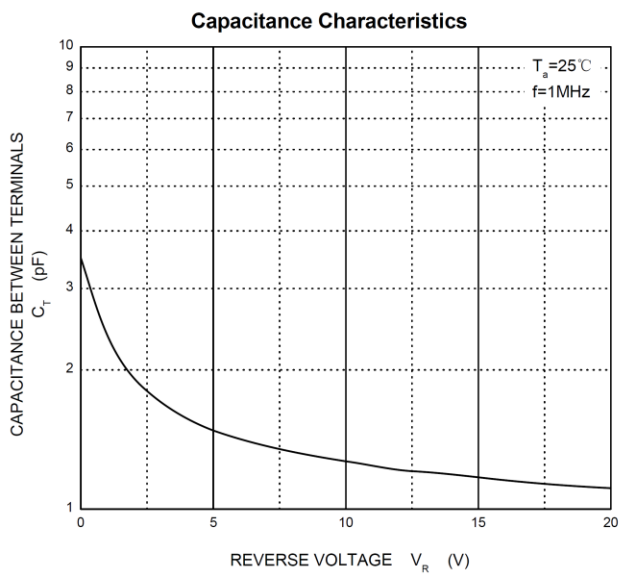
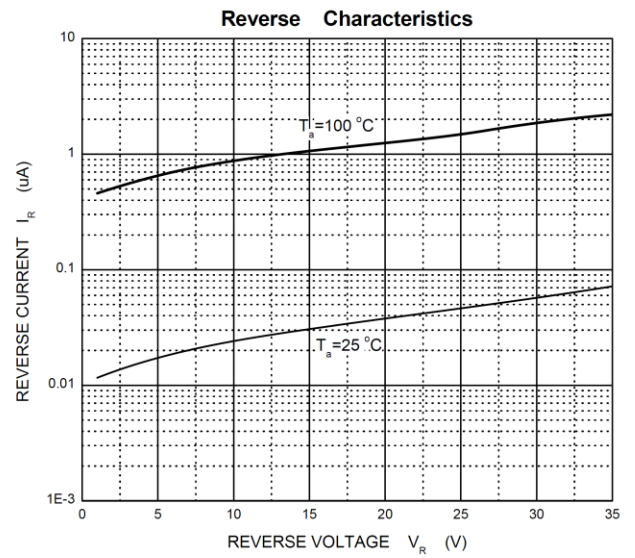
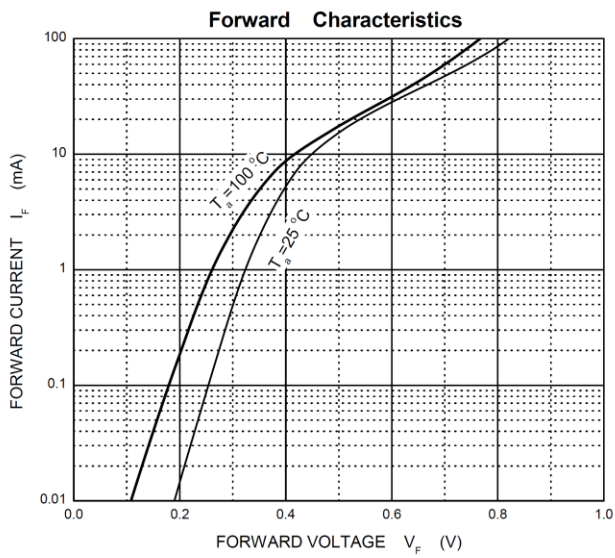
ABSOLUTE MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

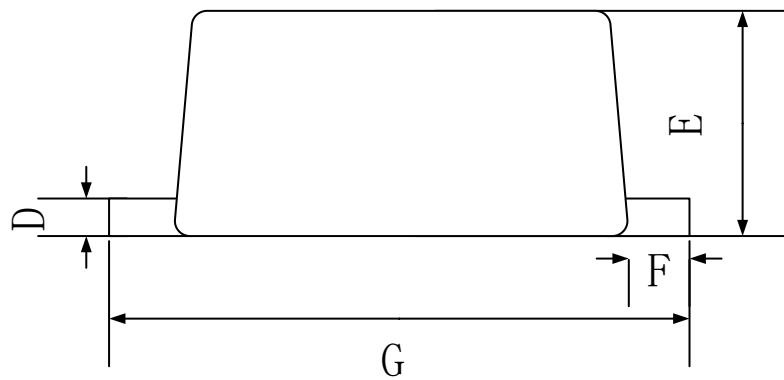
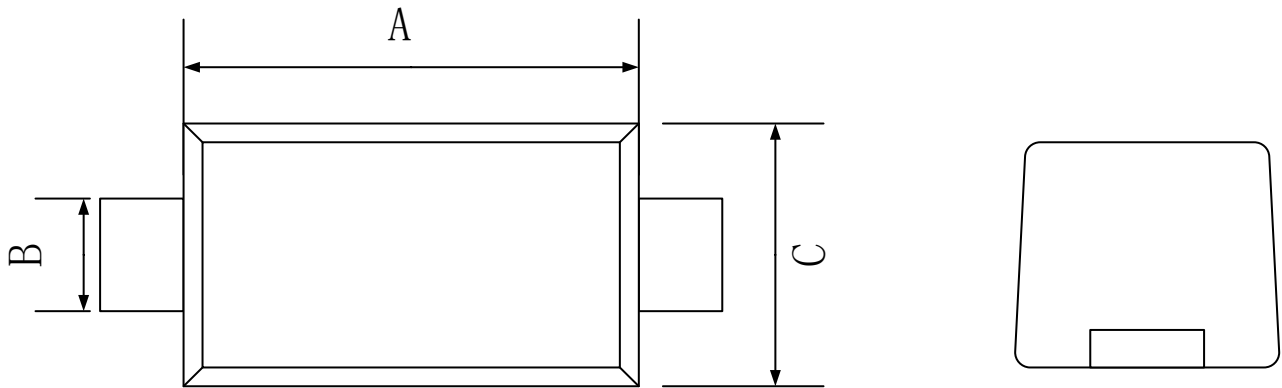
Parameter	Symbol	Value	Unit
DC reverse voltage	V _R	40	V
Mean rectifying current	I _O	30	mA
Non-repetitive Peak Forward Surge Current @ t=8.3ms	I _{FSM}	200	mA
Power Dissipation	P _D	0.15	W
Thermal Resistance from Junction to Ambient	R _{θJA}	667	°C/W
Junction Temperature	T _J	125	°C
Storage Temperature Range	T _{STG}	-55 ~ +150	°C

ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Reverse voltage	V _{BR}	I _R =100uA	40			V
Forward voltage	V _F	I _F =1mA			0.37	V
Reverse current	I _R	V _R =30V			0.5	μA
Capacitance between terminals	C _T	V _R =1V,f=1MHZ		2		pF

Typical Characteristics



SOD-523 Package Outline Dimensions


Symbol	Dimensions In Millimeters		
	Min.	Typ.	Max.
A	1.10	1.20	1.30
B	0.25	0.30	0.35
C	0.75	0.80	0.85
D	0.08	0.10	0.15
E	0.45	0.65	0.70
F	0.20 REF		
G	1.50	1.60	1.70